

**TO-92 Plastic-Encapsulate Transistors****2SA1296** TRANSISTOR (PNP)**FEATURES**

Power dissipation

$$P_{CM} : 0.75 \text{ W (Tamb=25°C)}$$

Collector current

$$I_{CM} : -2 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -20 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$

TO-92

1. EMITTER
2. COLLECTOR
3. BASE

**ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.1\text{mA}, I_E = 0$	-20			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10\text{mA}, I_B = 0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.1\text{mA}, I_C = 0$	-6			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -6\text{V}, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -2\text{V}, I_C = -0.1\text{A}$	120		400	
	$h_{FE(2)}$	$V_{CE} = -2\text{V}, I_C = -2\text{A}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}, I_B = -0.1\text{A}$			-0.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = -2\text{V}, I_C = -0.1\text{A}$			-0.85	V
Transition frequency	f_T	$V_{CE} = -2\text{V}, I_C = -0.5\text{A}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$		40		pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Y	GR
Range	120-240	200-400
Marking		